

Dual N-Channel, Digital FET

FDG6301N-F085

Features

- 25 V, 0.22 A Continuous, 0.65 A Peak
- $R_{DS(ON)} = 4 \Omega @ V_{GS} = 4.5 V$,
- $R_{DS(ON)} = 5 \Omega @ V_{GS} = 2.7 V$.
- Very Low Level Gate Drive Requirements allowing Directop–
eration in 3 V Circuits ($V_{GS(th)} < 1.5 V$)
- Gate–Source Zener for ESD Ruggedness ($>6 kV$ Human Body
Model)
- Compact Industry Standard SC70–6 Surface Mount Package.
- AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS
Compliant

Applications

- Low Voltage Applications as a Replacement for Bipolar Digital
Transistors and Small Signal MOSFETs

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	8	V
I_D	Drain Current Continuous	0.22	A
	Pulsed	0.65	
P_D	Power Dissipation	0.3	W
T_J, T_{STG}	Operating and Storage Temperature	–55 to 150	$^\circ C$
ESD	Electrostatic Discharge Rating MIL–STD–883D Human Body Model (100 pF / 1500 W)	6.0	kV
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	$^\circ C/W$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $R_{\theta JA}$ is the sum of the junction–to–case and case–to–ambient thermal resistance, where the case thermal reference is defined as the Solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. $R_{\theta JA} = 415 \text{ }^\circ C/W$ on minimum pad mounting on FR–4 board in still air.
2. A suffix as “...F085P” has been temporarily introduced in order to manage a double source strategy as ON Semiconductor has officially announced in August 2014.
3. Pulse Test: Pulse Width $< 300 \mu s$, Duty Cycle $< 2.0\%$

ORDERING INFORMATION

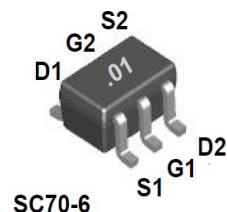
Device	Device Marking	Package	Shipping†
FDG6301N–F085	FDG6301N	SC–88 (SC–70 6 Lead) (Pb–Free, Halogen Free)	3,000 units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

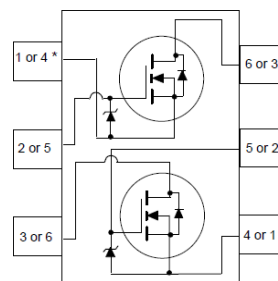


ON Semiconductor®

www.onsemi.com



SC–88 (SC–70 6 Lead), 1.25x2
CASE 419AD



FDG6301N-F085

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
-----------	--------	-----------------	-----	-----	-----	-------

Off Characteristics

Drain to Source Breakdown Voltage	B_{VDSS}	$I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	25			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20 \text{ V}$, $V_{GS} = 0 \text{ V}$			1	μA
					10	
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 8 \text{ V}$			± 100	nA

On Characteristics

Gate to Source Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$, $I_D = 250 \mu\text{A}$	0.65	0.85	1.5	V
Drain to Source On Resistance	$r_{DS(on)}$	$I_D = 0.22 \text{ A}$, $V_{GS} = 4.5 \text{ V}$		2.6	4	Ω
		$I_D = 0.19 \text{ A}$, $V_{GS} = 2.7 \text{ V}$		3.7	5	
		$I_D = 0.22 \text{ A}$, $V_{GS} = 4.5 \text{ V}$, $T_J = 125^\circ\text{C}$		5.3	7	
On-State Drain Current	$I_{D(on)}$	$V_{GS} = 4.5 \text{ V}$, $V_{DS} = 5 \text{ V}$	0.22			
Forward Transconductance	g_{FS}	$I_D = 0.22 \text{ A}$, $V_{DS} = 5 \text{ V}$		0.2		s

Dynamic Characteristics

Input Capacitance	C_{iss}	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		9.5		pF
Output Capacitance	C_{oss}			6		pF
Reverse Transfer Capacitance	C_{rss}			4.5		pF
Total Gate Charge at -4.5 V	$Q_{g(TOT)}$	$V_{GS} = 0 \text{ to } 4.5 \text{ V}$; $V_{DD} = 5 \text{ V}$, $I_D = 0.22 \text{ A}$		0.29	0.4	nC
Gate to Source Gate Charge	Q_{gs}			0.12		
Gate to Drain "Miller" Charge	Q_{gd}			0.03		

Switching Characteristics

Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 5 \text{ V}$, $I_D = 0.5 \text{ A}$, $V_{GS} = 4.5 \text{ V}$, $R_{GEN} = 50 \Omega$		5	10	ns
Rise Time	t_r			4.5	10	ns
Turn-Off Delay Time	$t_{d(off)}$			4	8	ns
Fall Time	t_f			3.2	7	ns

Drain-Source Diode Characteristics

Maximum Continuous Source Current	I_S				0.25	A
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 0.25 \text{ A}$, $V_{GS} = 0 \text{ V}$		0.8	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

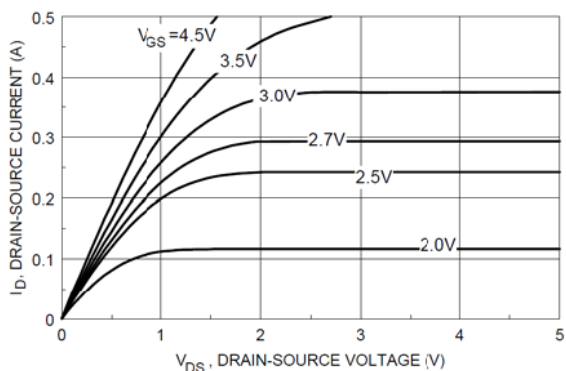


Figure 1. On-Region Characteristics

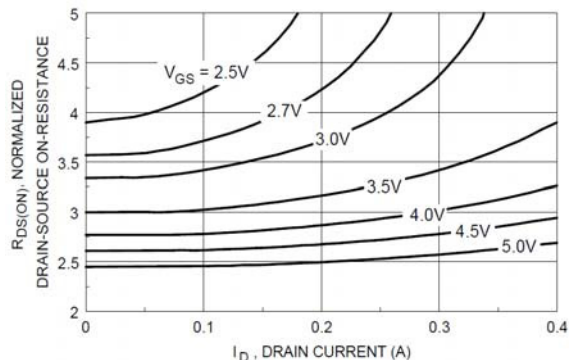


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

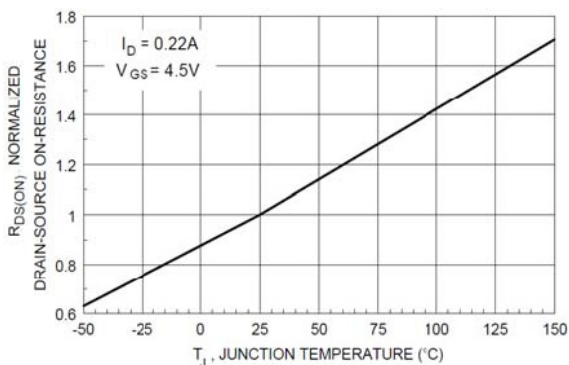


Figure 3. On-Resistance Variation with Temperature

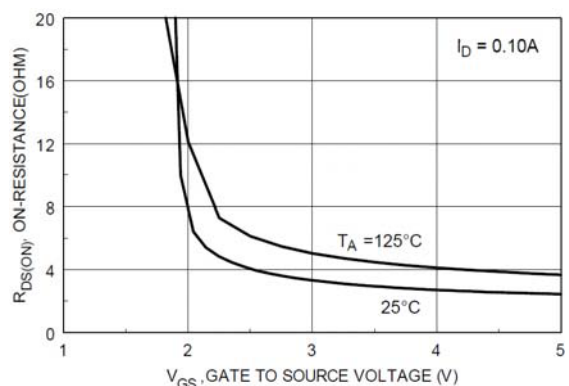


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

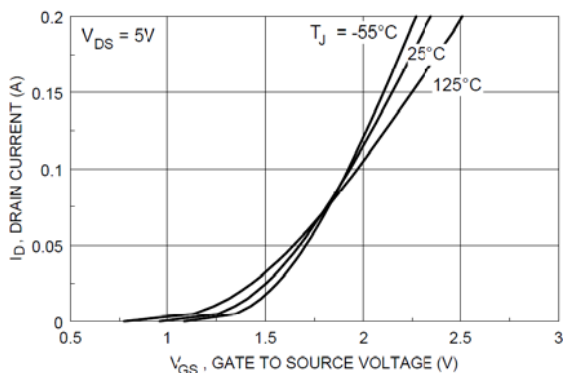


Figure 5. Transfer Characteristics

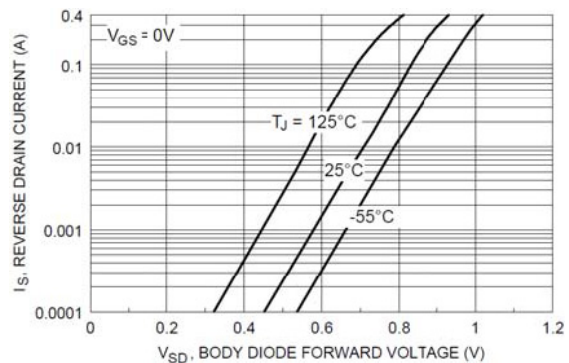


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

FDG6301N-F085

TYPICAL CHARACTERISTICS

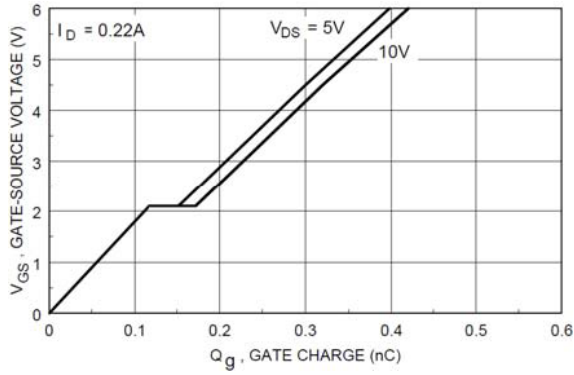


Figure 7. Gate Charge Characteristics

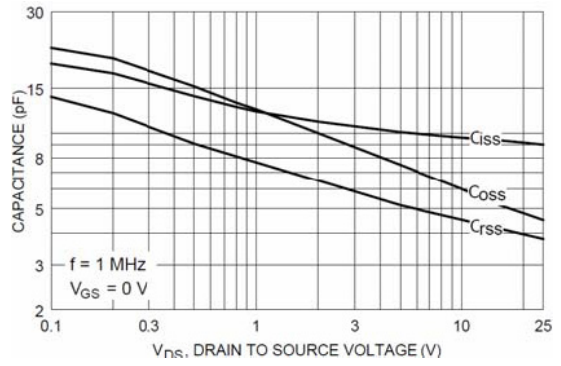


Figure 8. Capacitance Characteristics

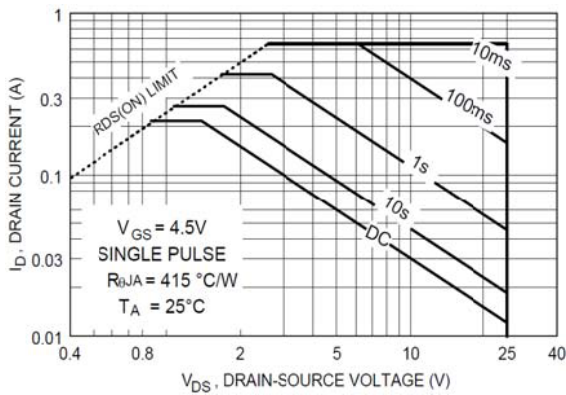


Figure 9. Maximum Safe Operating Area

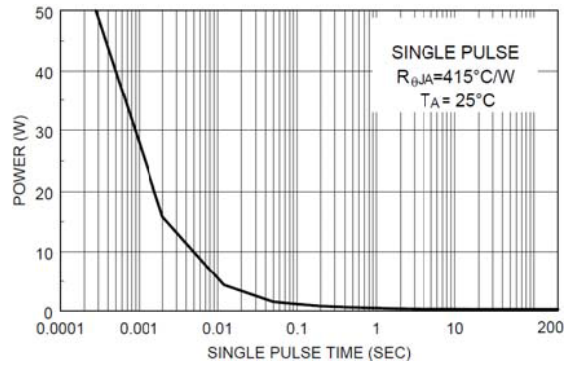


Figure 10. Single Pulse Maximum Power Dissipation

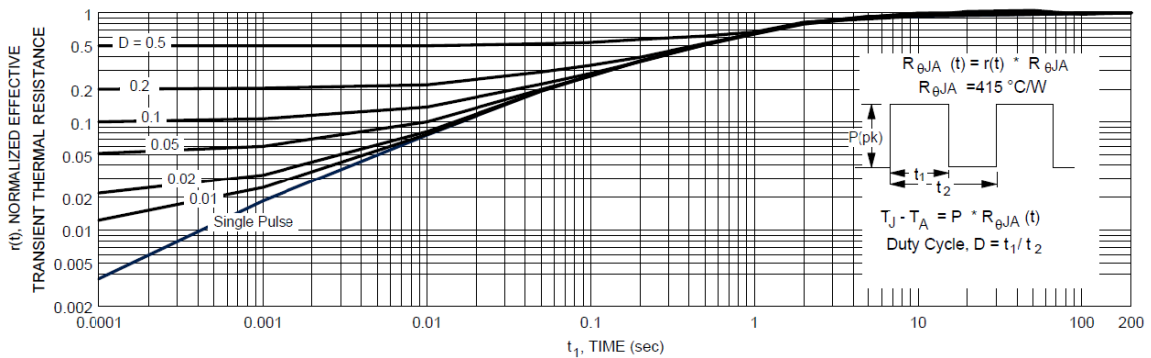


Figure 11. Transient Thermal Response Curve

MECHANICAL CASE OUTLINE

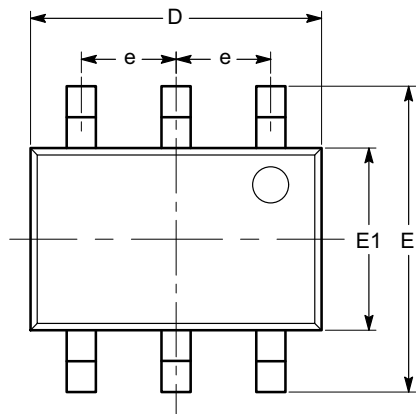
PACKAGE DIMENSIONS

ON Semiconductor®



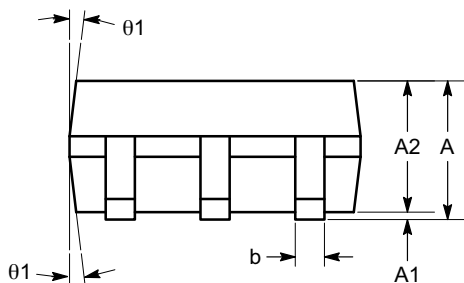
SC-88 (SC-70 6 Lead), 1.25x2
CASE 419AD-01
ISSUE A

DATE 07 JUL 2010

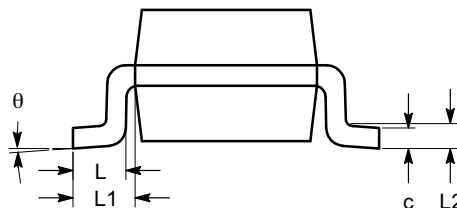


TOP VIEW

SYMBOL	MIN	NOM	MAX
A	0.80		1.10
A1	0.00		0.10
A2	0.80		1.00
b	0.15		0.30
c	0.10		0.18
D	1.80	2.00	2.20
E	1.80	2.10	2.40
E1	1.15	1.25	1.35
e	0.65 BSC		
L	0.26	0.36	0.46
L1	0.42 REF		
L2	0.15 BSC		
θ	0°		8°
θ_1	4°		10°



SIDE VIEW



END VIEW

Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MO-203.

DOCUMENT NUMBER:	98AON34266E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SC-88 (SC-70 6 LEAD), 1.25X2	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:
Voice Mail: 1 800-282-9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative